

20kV 10mA HIGH VOLTAGE DIODES

G20FP is high reliability resin molded type high voltage diode in small size package which is sealed a multilayered mesa type silicon chip by epoxy resin.

Features

- High speed switching
- High Current
- High surge resistivity for CRT discharge
- High reliability design
- High Voltage

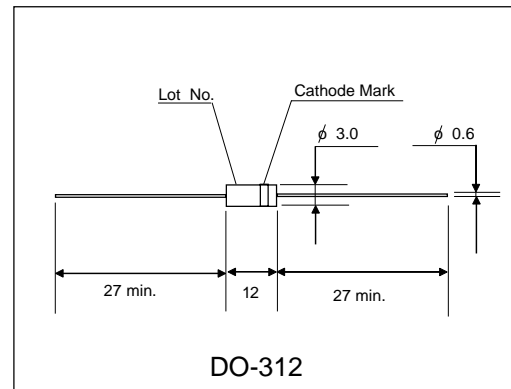
Applications

- X light Power supply
- Laser
- Voltage doubler circuit
- Microwave emission power

Maximum Ratings and Characteristics

- Absolute Maximum Ratings

Outline Drawings : mm



Cathode Mark

| Type | Mark |
|-------|------|
| G20FP | |

| Items | Symbols | Condition | G20FP | Units |
|--------------------------------------|-----------|-------------------------|-------------|-------------------|
| Repetitive Peak Reverse Voltage | V_{RRM} | | 20 | kV |
| Average Output Current | I_o | Ta=25°C, Resistive Load | 10 | mA |
| Surge Current | I_{FSM} | | 0.8 | A _{peak} |
| Junction Temperature | T_j | | 125 | °C |
| Allowable Operation Case Temperature | T_c | | 120 | °C |
| Storage Temperature | T_{stg} | | -40 to +125 | °C |

Electrical Characteristics (Ta=25°C Unless otherwise specified)

| Items | Symbols | Conditions | G20FP | Units |
|-------------------------------|----------|-------------------------------|-------|-------|
| Maximum Forward Voltage Drop | V_F | at 25°C, $I_F = I_{F(AV)}$ | 55 | V |
| Maximum Reverse Current | IR1 | at 25°C, $V_R = V_{RRM}$ | 2.0 | uA |
| | IR2 | at 100°C, $V_R = V_{RRM}$ | 5.0 | uA |
| Maximum Reverse Recovery Time | T_{rr} | at 25°C | 100 | nS |
| Junction Capacitance | C_j | at 25°C, $V_R = 0V, f = 1MHz$ | -- | pF |